BC212
BC212A
BC212B

SILICON
PNP TRANSISTORS

TO-92 CASE

www.centralsemi.com

DESCRIPTION:
The CENTRAL SEMICONDUCTOR BC212 series are silicon PNP transistors designed for low noise, high gain amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	200	mA
Power Dissipation	P_D	300	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	416	°C\W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=30V		15	nA
I_{EBO}	V_{EB}=4.0V		15	nA
BV_{CBO}	I_C=10μA	60		V
BV_{CEO}	I_C=2.0mA	50		V
BV_{EBO}	I_E=10μA	5.0		V
$V_{CE(SAT)}$	I_C=10mA, I_B=500μA		0.25	V
$V_{CE(SAT)}$	I_C=100mA, I_B=5.0mA		0.60	V
$V_{BE(SAT)}$	I_C=100mA, I_B=5.0mA		1.4	V
$V_{BE(ON)}$	V_{CE}=5.0V, I_C=2.0mA	0.60	0.72	V
h_{FE}	V_{CE}=5.0V, I_C=2.0mA (BC212)	60	400	
h_{FE}	V_{CE}=5.0V, I_C=2.0mA (BC212A)	100	300	
h_{FE}	V_{CE}=5.0V, I_C=2.0mA (BC212B)	200	400	
f_T	V_{CE}=5.0V, I_C=10mA, f=100MHz	200		MHz
C_{ob}	V_{CB}=10V, I_C=0, f=1.0MHz		6.0	pF
NF	V_{CE}=5.0V, I_C=200μA, f=1.0kHz, R_S=2.0kΩ		10	dB

R1 (19-May 2017)

BC212
BC212A
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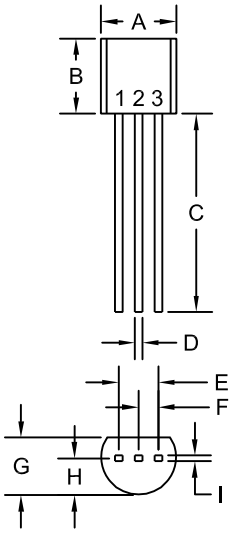
TO-92 CASE - MECHANICAL OUTLINE



R1

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:
1) Collector
2) Base
3) Emitter

MARKING:
FULL PART NUMBER